Title (en)

MICROWAVE MONOLITHIC INTEGRATED CIRCUIT (MMIC) AMPLIFIED HAVING DE-Q'ING SECTION WITH RESISTIVE VIA

Title (de)

VERSTÄRKTE MONOLITHISCHE MIKROWELLENINTEGRIERTE SCHALTUNG (MMIC) MIT EINEM DE-Q'ING-ABSCHNITT MIT RESISTIVER DURCHKONTAKTIERUNG

Title (fr)

CIRCUIT INTÉGRÉ MONOLITHIQUE HYPERFRÉQUENCE (MMIC) AMPLIFIÉ AYANT UNE SECTION DE SUPPRESSION DES OSCILLATIONS AVEC UN TROU D'INTERCONNEXION RÉSISTIF

Publication

**EP 3482494 A1 20190515 (EN)**

Application

**EP 17734194 A 20170614**

Priority

- US 201615201905 A 20160705
- US 2017037375 W 20170614

Abstract (en)

[origin: WO2018009314A1] A microwave amplifier having a field effect transistor formed on an upper surface of a substrate. A de-Q'ing section connected to the field effect transistor includes: a de-Q'ing resistive via that passes through the substrate; and a de-Q'ing capacitor having one plate thereof connected a ground plane conductor through the de-Q'ing resistive via.

IPC 8 full level

**H03F 1/56** (2006.01); **H01L 23/467** (2006.01); **H03F 3/189** (2006.01); **H03F 3/60** (2006.01)

CPC (source: EP KR)

**H01L 21/76898** (2013.01 - EP KR); **H01L 23/481** (2013.01 - EP KR); **H01L 23/647** (2013.01 - EP KR); **H01L 23/66** (2013.01 - EP); **H01L 27/0617** (2013.01 - KR); **H03F 1/565** (2013.01 - EP KR); **H03F 3/189** (2013.01 - EP KR); **H03F 3/607** (2013.01 - EP KR); H01L 23/5228 (2013.01 - EP); H01L 2224/4813 (2013.01 - EP)

Citation (search report)

See references of WO 2018009314A1

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

DOCDB simple family (publication)

**WO 2018009314 A1 20180111**; EP 3482494 A1 20190515; JP 2019525556 A 20190905; KR 20190025690 A 20190311

DOCDB simple family (application)

**US 2017037375 W 20170614**; EP 17734194 A 20170614; JP 2018568814 A 20170614; KR 20197003179 A 20170614